

Vishay Siliconix

HALOGEN

1.7 Ω , Low On Resistance, +12 V, +5 V, +3 V, ± 5 V, SPST Switches

DESCRIPTION

The DG9421E and DG9422E are monolithic single-pole-single-throw (SPST) analog switches. The DG9421E has a normally closed function. The DG9422E has a normally open function.

Processed with high density BiCMOS technology, the parts achieve low resistance, fast switching speed, low power dissipation, high -3dB bandwidth, and low voltage logic control threshold.

The DG9421E and DG9422E operate on single and dual supplies. Single supply voltage ranges from +3 V to +16 V while dual supply operation is recommended with \pm 3 V to \pm 8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The low and flat on resistance over the full input signal voltage range brings excellent linearity, reduces insertion loss and signal distortion, makes them ideal for data acquisition and programmable gain control applications. These switch characters also make them ideal fit for audio signal switch and reed relay replacement.

Operation temperature is specified from -40 °C to +85 °C. The DG9421E and DG9422E are available in 6 lead TSSOP packages.

BENEFITS

- Wide operation voltage range
- · Low signal errors and distortion
- · Fast switching time
- Simple interfacing

FEATURES

- 3 V to 16 V single supply or ± 3 thru ± 8 V dual supply operation
- Low on resistance: 1.7 Ω typical at 12 V
- 2.4 V logic compatible for control
- Bi-directional rail to rail signal switching
- · Fast switching speed
- High bandwidth: 161 MHz
- Control logic input can be over V+
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

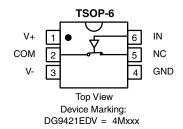
Note

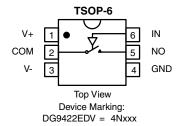
* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- · Automatic test equipment
- Data acquisition systems
- · Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video signal routing
- Relay replacement
- Battery powered systems
- Computer peripherals
- · Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE						
LOGIC	LOGIC DG9421E DG9422E					
0	On	Off				
1	Off	On				

Notes

- Logic "0" ≤ 0.8 V
- Logic "1" ≥ 2.4 V
- Switches shown for logic "0" input

ORDERING INFORMATION					
TEMP. RANGE	RANGE PACKAGE PART NUMBER				
-40 °C to +85 °C 6-pin TSOP		DG9421EDV-T1-GE3			
-40 C to +65 C	6-pin TSOP	DG9422EDV-T1-GE3			

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER		LIMIT	UNIT				
V+ reference to V-	-0.3 to +18						
IN		-0.3 to +18	V				
V+ reference to GND	-0.3 to +18	V					
GND reference to V-		-0.3 to +18					
COM, NC, NO ^a		(V-) - 0.3 V to (V+) + 0.3 V or 50 mA, whichever occurs first	-				
Continuous current (any terminal)		50	A				
Peak current, NO, NC or COM (pulsed at 1	ms, 10 % duty cycle)	100	mA				
Storage temperature		-65 to +150	°C				
Power dissipation (packages) b	6-pin TSOP ^c	570	mW				
ESD / HBM JS-001 2000							
ESD / CDM JS-002		2000	V				
Latch up per JEDEC78 300			mA				

Notes

- a. Signals on NO, NC, COM exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 25 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS a (Single suppl	y 12 V)					
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	LIMITS -40 °C to +85°C			UNIT
		$V+ = 12 V, V- = 0 V, V_{IN} = 2.4 V, 0.8 V$ f		MIN. d	TYP. c	MAX. d	
Analog Switch							
Analog signal range a	V _{ANALOG}		Full	0	-	12	V
Drain-source	D	V+ = 10.8 V, V- = 0 V,	Room	-	1.7	2.7	Ω
on-resistance	R _{DS(on)}	$I_{NO/NC} = 5 \text{ mA}, V_{COM} = 2 \text{ V} / 9 \text{ V}$	Full	-	-	3.2	5.2
	1		Room	-1	± 0.004	1	
Switch off	I _{NO/NC(off)}	V _{COM} = 1 V / 11 V, V _{NO/NC} = 11 V / 1 V	Full	-10	± 1.06	10	
leakage current ^g	1	$\mathbf{v}_{\text{COM}} = \mathbf{i} \mathbf{v} / \mathbf{i} \mathbf{i} \mathbf{v}, \mathbf{v}_{\text{NO/NC}} = \mathbf{i} \mathbf{i} \mathbf{v} / \mathbf{i} \mathbf{v}$	Room	-1	± 0.004	1	nA
	I _{COM(off)}		Full	-10	± 0.23	10	II/A
Channel-on	1	$V_{NO/NC} = V_{COM} = 11 \text{ V} / 1 \text{ V}$	Room	-1	± 0.002	1	
leakage current ^g	I _{COM(on)}	$v_{NO/NC} = v_{COM} = 11 v 7 1 v$	Full	-10	± 0.454	10	
Digital Control							
Input current, V _{IN} low	I _{IL}	V _{IN} under test = 0.8 V	Full	-1	0.001	1	μA
Input current, V _{IN} high	I _{IH}	V_{IN} under test = 2.4 V	Full	-1	0.001	1	μΑ
Dynamic Characteristics							
Turn-on time e	+		Room	-	28	36	
rum-on time °	t _{ON}	$R_1 = 300 \Omega$, $C_1 = 35 pF$, $V_S = 5 V$	Full	-	-	41]
Turn-off time e	+	$n_L = 300 \Omega_2$, $O_L = 35 \text{ pr}$, $V_S = 5 \text{ V}$	Room	-	12	20	ns
rum-on time •	t _{OFF}		Full	-	-	22	
Charge injection ^e	Q	$V_{g} = 0 \text{ V}, R_{g} = 0 \Omega, C_{L} = 1 \text{ nF}$	Room	-	19	-	рС
Bandwidth ^e	BW	$R_L = 50 \Omega, C_L = 5 pF$	Room	-	161	-	MHz
Off-isolation e	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-58	-	dB
Source off capacitance e	C _{NO/NC(off)}		Room	-	34	-	
Drain off capacitance e	C _{COM(off)}	f = 1 MHz	Room	-	36	-	pF
Channel on capacitance e	C _{COM(on)}		Room	-	68	-	
Power Supplies							
Positive supply current	l+		Room	-	0.001	1	
Fositive Supply Current	I+	V _{IN} = 0 V or 12 V	Full	-	-	5	
Negative expely express	I-		Room	-1	-0.001	-	
Negative supply current	I-		Full	-5	-	-	μA
Ground current	1		Room	-1	-0.001	-	
Ground current	I _{GND}		Full	-5	-	-	



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. b	LIMITS -40 °C to +85 °C			UNIT
		V+ = 5 V, V- = -5 V, V_{IN} = 2.4 V, 0.8 V f		MIN. d	TYP. °	MAX. d	
Analog Switch							
Analog signal range e	V _{ANALOG}		Full	-5	-	5	V
Drain-source	Ь	V+ = 5 V, V- = 5 V	Room	-	1.9	2.9	Ω
on-resistance	R _{DS(on)}	$I_{NO/NC} = 5 \text{ mA}, V_{COM} = \pm 3.5 \text{ V}$	Full	-	-	3.4	52
			Room	-1	± 0.004	1	
Switch off	I _{NO/NC(off)}	V+ = 5.5 V, V- = 5.5 V	Full	-10	± 1.012	10	
leakage current ^g		$V_{COM} = \pm 4.5 \text{ V}, V_{NO/NC} = \mp 4.5 \text{ V}$	Room	-1	± 0.003	1	nA
	ICOM(off)		Full	-10	± 0.188	10	ΠA
Channel-on		V+ = 5.5 V, V- = -5.5 V	Room	-1	± 0.002	1	
leakage current ^g	I _{COM(on)}	$V_{NO/NC} = V_{COM} = \pm 4.5 \text{ V}$	Full	-10	± 0.425	10	
Digital Control					•		L
Input current, V _{IN} low ^e	I _{IL}	V _{IN} under test = 0.8 V	Full	-1	0.001	1	
Input current, V _{IN} high ^e	I _{IH}	V _{IN} under test = 2.4 V	Full	-1	1 0.001 1 P	μΑ	
Dynamic Characteristics					•		'
Turn on time			Room	-	39	54	- ns
Turn-on time	t _{ON}	D 000 0 0 05 EV 05 V	Full	-	-	62	
T (()'		$R_L = 300 \Omega$, $C_L = 35 pF$, $V_S = \pm 3.5 V$	Room	-	28	33	
Turn-off time	t _{OFF}		Full	-	-	42	
Charge injection e	Q	$V_{q} = 0 \text{ V}, R_{q} = 0 \Omega, C_{L} = 1 \text{ nF}$	Room	-	57	-	рС
Bandwidth ^e	BW	$R_L = 50 \Omega$, $C_L = 5 pF$	Room	-	179	-	MHz
Off-isolation e	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-	-58	-	dB
Source off capacitance e	C _{NO/NC(off)}		Room	-	34	-	
Drain off capacitance e	C _{COM(off)}	f = 1 MHz	Room	-	36	-	рF
Channel on capacitance e	C _{COM(on)}		Room	-	68	-	
Power Supplies	, , ,				•		'
Design and a section		V _{IN} = 0 V or 5 V	Room	-	0.001	1	
Positive supply current ^e	l+		Full	-	-	5	μΑ
N	1 .		Room	-1	-0.001	-	
Negative supply current e	I-		Full	-5	-	-	
0 1 10			Room	-1	-0.001	-	
Ground current e	I _{GND}		Full	-5	_	_	1



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SPECIFICATIONS ^a (Single supply 5 V)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP.b	LIMITS -40 °C to +85 °C			UNIT	
		$V+ = 5 V$, $V- = 0 V$, $V_{IN} = 2.4 V$, $0.8 V$ f		MIN. d	TYP. c	MAX. d		
Analog Switch								
Analog signal range e	V _{ANALOG}		Full	0	-	5	V	
Drain-source	D	$V+ = 4.5 \text{ V}, I_{NO/NC} = 5 \text{ mA},$	Room	ı	3.04	5.4	Ω	
on-resistance	R _{DS(on)}	$V_{COM} = 1 \text{ V}, 3.5 \text{ V}$	Full	-	-	7	2.2	
Dynamic Characteristics								
Turn-on time e	+	R_L = 300 Ω, C_L = 35 pF, V_S = 3.5 V	Room	-	57	82	- ns	
rum-on time -	t _{ON}		Hot	ı	-	95		
Turn-off time e	+		Room	ı	24	34		
rum-on time s	t _{OFF}		Hot	-	-	40		
Charge injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	-	12	-	рC	
Power Supplies								
Docitive august ourrent 6	l+		Room	-	0.001	1		
Positive supply current ^e			Hot	-	-	5		
Negative supply current e	I-	V _{IN} = 0 V or 5 V	Room	-1	-0.001	-		
Negative Supply Currett	Į-		Hot	-5	-	-	μΑ	
Ground current e	Draward accorded		Room	-1	-0.001	=		
Ground Current	I _{GND}		Hot	-5	-	-		



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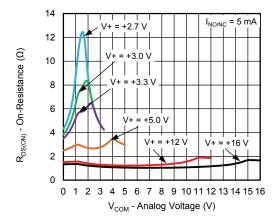
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SPECIFICATIONS a (Single supp	ly 3 V)					
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. b	LIMITS -40 °C to +85 °C			UNIT
		V+ = 3 V, V- = 0 V, V_{IN} = 2.4 V, 0.4 V f		MIN. d	TYP. c	MAX. d	
Analog Switch							
Analog signal range e	V _{ANALOG}		Full	0	-	3	٧
Drain-source	D	V+ = 2.7 V, V- = 0 V	Room	1	7.3	11.5	Ω
on-resistance	R _{DS(on)}	$I_{NO/NC} = 5 \text{ mA}, V_{COM} = 0.5 \text{ V}, 2.2 \text{ V}$	Full	1	-	18	22
	lua nua ca		Room	-1	± 0.003	1	nA
Switch off	I _{NO/NC(off)}	V+ = 3.3 V, V- = 0 V	Full	-10	± 0.9	10	
leakage current ^g	1	$V_{NO/NC} = 1 V, 2 V, V_{COM} = 2 V, 1 V$	Room	-1	± 0.0008	1	
	I _{COM(off)}		Full	-10	± 0.042	10	
Channel-on		V+ = 3.3 V, V- = 0 V	Room	-1	± 0.0014	1	
leakage current ^g	I _{COM(on)}	$V_{COM} = V_{NO/NC} = 1 V, 2 V$	Full	-10	± 0.41	10	
Digital Control							
Input current, V _{IN} low ^e	I _{IL}	V_{IN} under test = 0.4 V	Full	-1	0.001	1	μA
Input current, V _{IN} high ^e	I _{IH}	V_{IN} under test = 2.4 V	Full	-1	0.001	1	μ
Dynamic Characteristics							
Turn-on time		$R_1 = 300 \Omega$, $C_1 = 35 pF$, $V_2 = 1.5 V$	Room	ı	124	215	
rum-on ume	t _{ON}		Full	1	-	222	ns
Turn-off time	+	$n_L = 300 \Omega$, $O_L = 33 \text{pr}$, $V_S = 1.3 \text{V}$	Room	-	58	101	
rum-on ume	t _{OFF}		Full	-	-	106	
Charge injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	-	6	-	рС
Off-isolation e	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-58	-	dB
Source off capacitance e	C _{NO/NC(off)}		Room	-	36	-	
Drain off capacitance e	C _{COM(off)}	f = 1 MHz	Room	-	38	-	pF
Channel on capacitance e	C _{COM(on)}		Room	-	70	-	

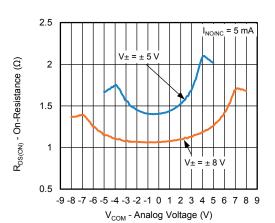
Notes

- a. Refer to PROCESS OPTION FLOWCHART
- b. Room = 25 $^{\circ}$ C, full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- e. Guaranteed by design, not subject to production test
- f. V_{IN} = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test

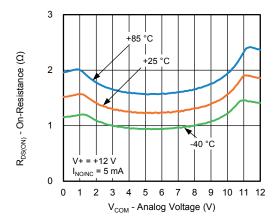




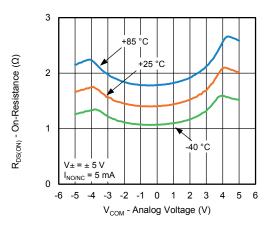
R_{ON} vs. V_{COM} and Single Supply Voltage



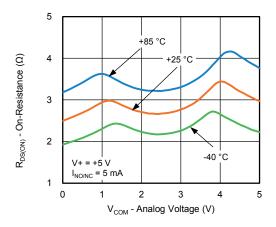
R_{ON} vs. V_{COM} and Dual Supply Voltage



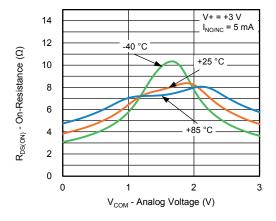
R_{DS(on)} vs. Analog Voltage and Temperature



R_{DS(on)} vs. Analog Voltage and Temperature

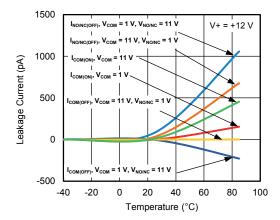


R_{DS(on)} vs. Analog Voltage and Temperature

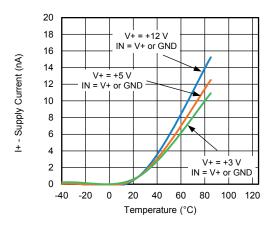


R_{DS(on)} vs. Analog Voltage and Temperature

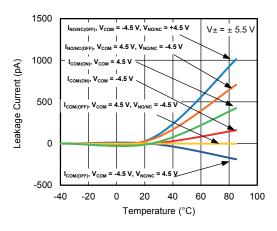




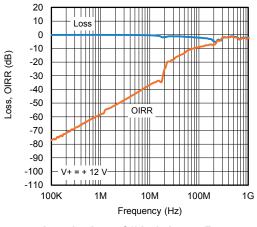
Leakage Current vs. Temperature



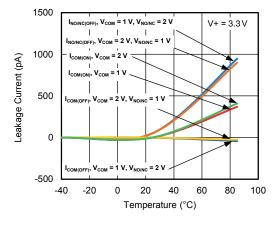
Supply Current vs. Temperature



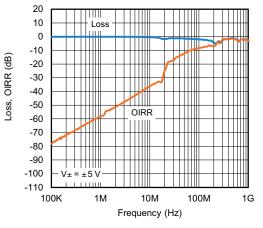
Leakage Current vs. Temperature



Insertion Loss, Off-Isolation vs. Frequency

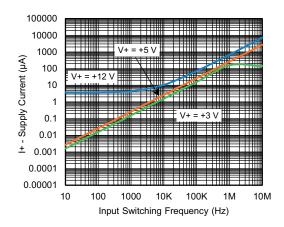


Leakage Current vs. Temperature

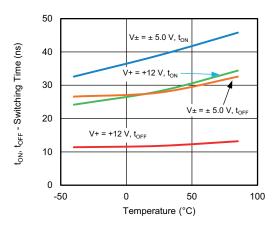


Insertion Loss, Off-Isolation vs. Frequency

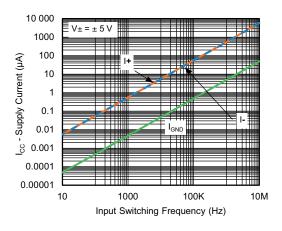




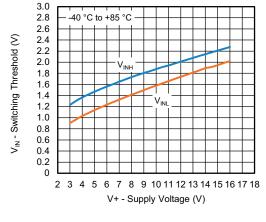
Supply Current vs. Input Switching Frequency



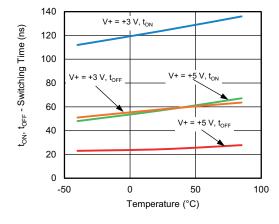
Switching Time vs. Temperature



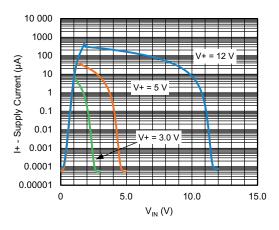
Supply Current vs. Input Switching Frequency



Switching Threshold vs. Supply Voltage

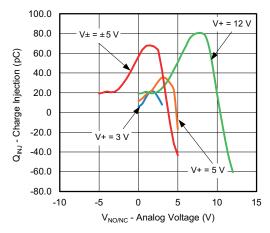


Switching Time vs. Temperature



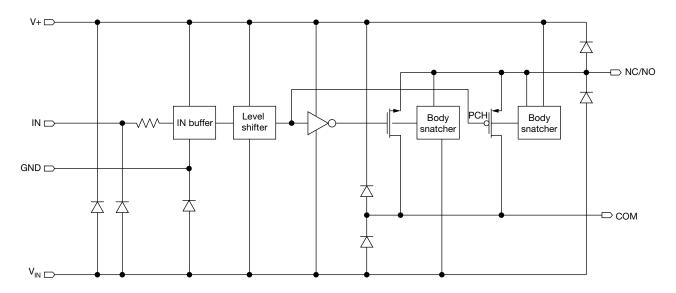
Supply Current vs. Enable Input Voltage





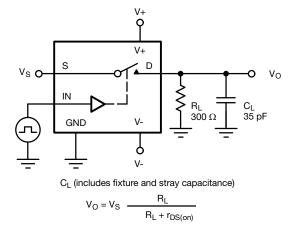
Charge Injection vs. Analog Voltage

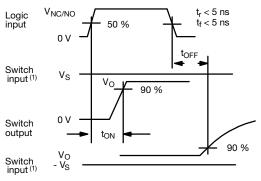
SCHEMATIC DIAGRAM (typical channel)





TEST CIRCUITS

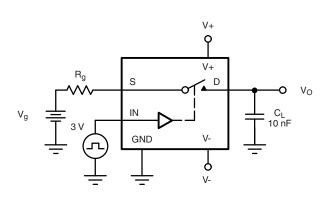


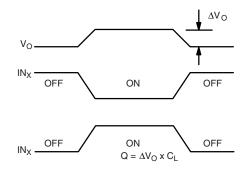


Note

(1) Logic input waveform is inverted for switches that have the opposite logic sense control

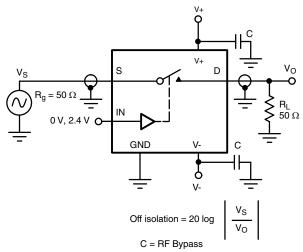
Fig. 1 - Switching Time





 $\ensuremath{\mathsf{IN}_X}$ dependent on switch configuration Input polarity determined by sense of switch.

Fig. 2 - Charge Injection





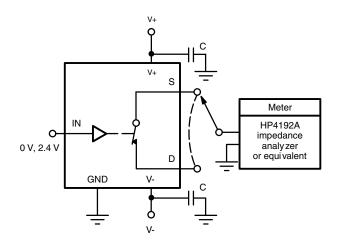


Fig. 4 - Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg275411.



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